

2SC2324(K)

Silicon NPN Epitaxial

HITACHI

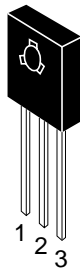
ADE-208-883 (Z)
1st. Edition
Sep. 2000

Application

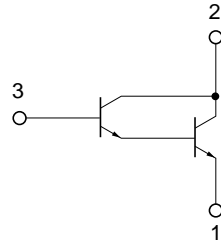
Low frequency power amplifier

Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_{C}	1	A
Collector peak current	$I_{\text{C(peak)}}$	2	A
Collector power dissipation	P_{C}	0.8	W
	P_{C}^{*1}	8	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

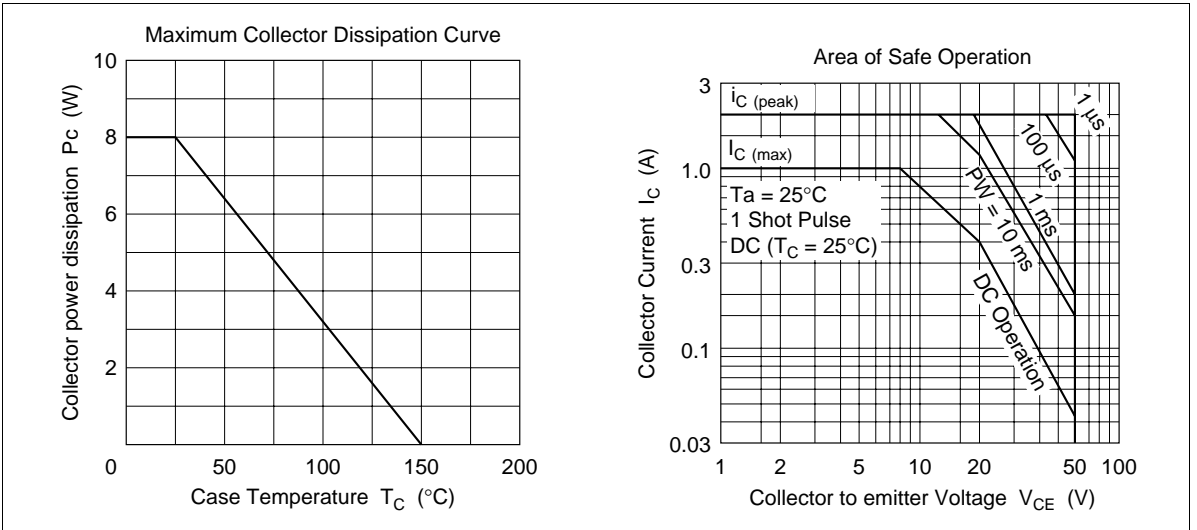
Note: 1. Value at $T_{\text{c}} = 25^\circ\text{C}$.

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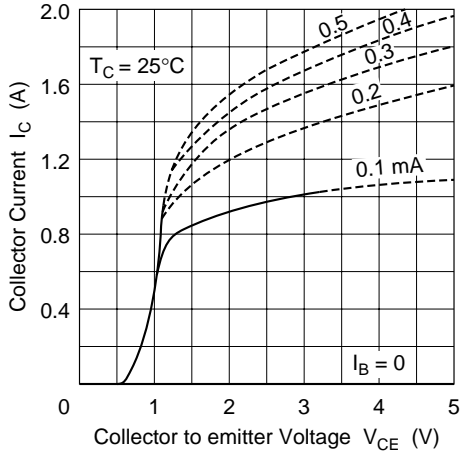
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 0.1 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 60 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE}	2000	—	—		$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	
Turn on time	t_{on}	—	100	—	ns	$V_{CC} = 12 \text{ V}$
Turn off time	t_{off}	—	600	—	ns	$I_C = 250 \text{ mA}, I_{B1} = -I_{B2} = 5 \text{ mA}$

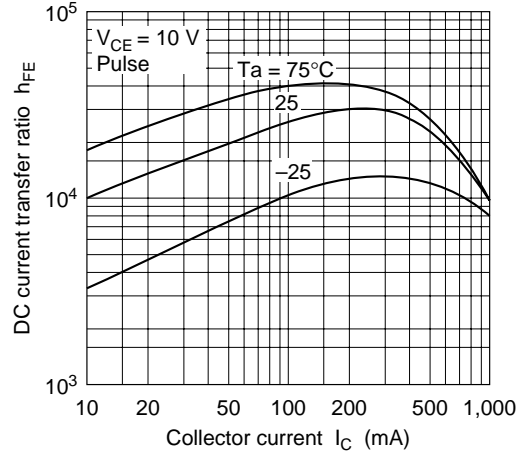
Note: 1. Pulse test.



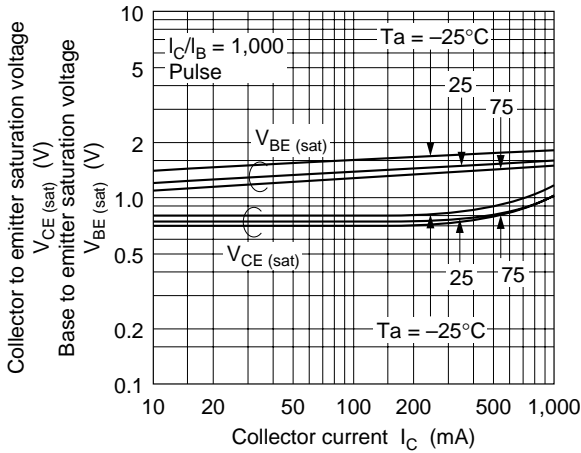
Typical Output Characteristics



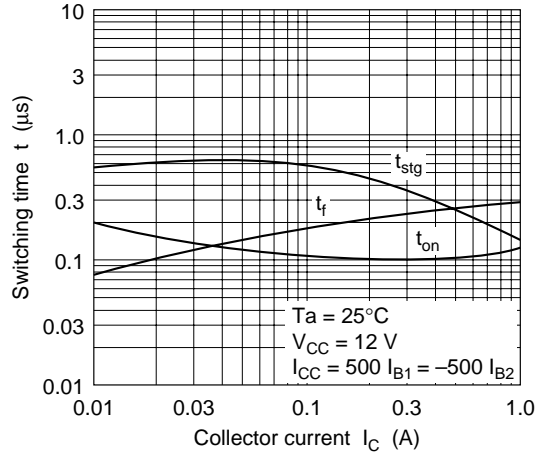
DC Current Transfer Ratio vs. Collector Current

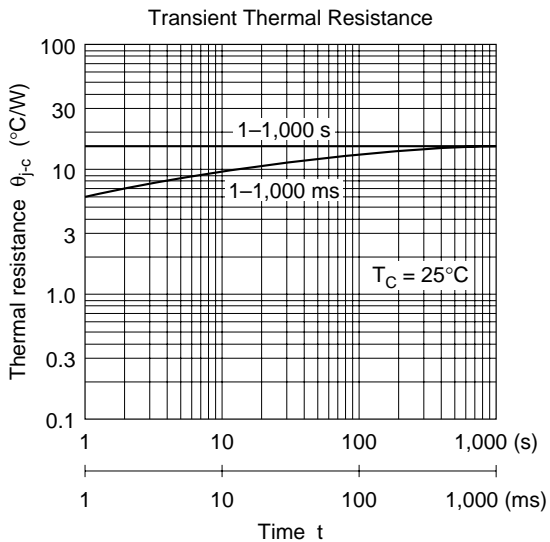


Saturation Voltage vs. Collector Current



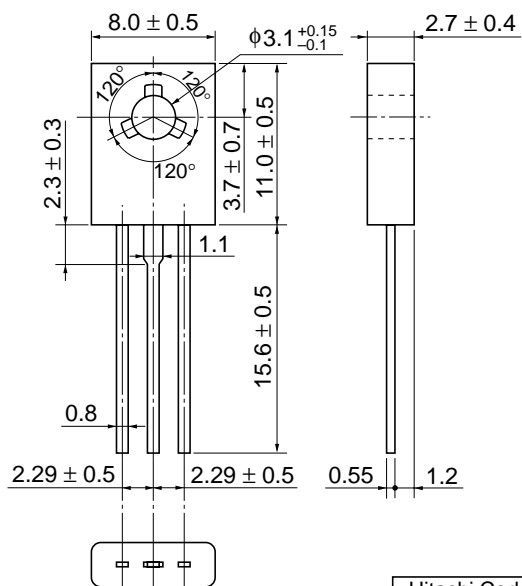
Switching Time vs. Collector Current





Package Dimensions

Unit: mm



Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Mass (reference value)	0.67 g

Cautions

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